<u>TOSHIBA</u>

TOSHIBA Photocoupler GaAs Ired & Photo-Thyristor

TLP741G

Office Machine Household Use Equipment Solid State Relay Switching Power Supply

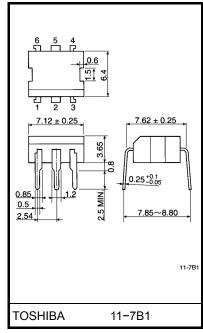
The TOSHIBA TLP741G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak off-state voltage: 400V(min.)
- Trigger LED current: 10mA(max.)
- On-state current: 150mA(max.)
- UL recognized: UL1577, file no. E67349
- BSI approved: BS EN60065: 2002 Certificate no. 8877 BS EN60950-1: 2002 Certificate no. 8878
- Isolation voltage: 4000V_{rms}(min.)
- Option (D4) type

VDE approved: DIN EN 60747-5-2 Certificate no. 40009302 Maximum operating insulation voltage: 630VPK Highest permissible over voltage: 6000VPK

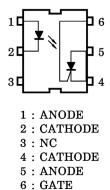
(Note) When a EN 60747-5-2 approved type is needed, please designate the "option (D4)"

		7.62mm pich standard type	10.16mm pich (LF2) type
•	Creepage distance:	7.0mm(min.)	8.0mm(min.)
	Clearance:	7.0mm(min.)	8.0mm(min.)
	Insulation thickness:	0.5mm(min.)	0.5mm(min.)



Weight: 0.35 g

Pin Configuration (top view)



Unit in mm

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	١ _F	60	mA
	Forward current derating (Ta ≥ 39°C)	ΔI _F / °C	-0.7	mA / °C
	Peak forward current (100µs pulse, 100pps)	I _{FP}	1	А
LED	Power dissipation	PD	100	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _D / °C	-1.0	mW / °C
	Reverse voltage	V _R	5	V
	Junction temperature	Tj	125	°C
	Peak forward voltage(R_{GK} = 27k Ω)	V _{DRM}	400	V
	Peak reverse voltage(R_{GK} = 27k Ω)	V _{RRM}	400	V
	On-state current	I _{T(RMS)}	150	mA
	On–state current derating (Ta ≥ 25°C)	ΔI _T / °C	-2.0	mA / °C
Detector	Peak on-state current (100µs pulse, 120pps)	I _{TP}	3	А
Dete	Peak one cycle surge current	ITSM	2	А
	Peak reverse gate voltage	V _{GM}	5	V
	Power dissipation	PD	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _D / °C	-2.0	mW / °C
	Junction temperature	Tj	100	°C
Storage temperature range		T _{stg}	-55~125	°C
Operating temperature range		T _{opr}	-55~100	°C
Lead s	oldering temperature (10s)	T _{sol}	260	°C
Total p	package power dissipation	PT	250	mW
Total package power dissipation derating $(Ta \ge 25^{\circ}C)$		ΔP _T / °C	-3.3	mW / °C
Isolatio	on voltage (AC, 1 min., R.H. ≤ 60%)	BVS	4000	$V_{ m rms}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	—	—	120	Vac
Forward current	١ _F	15	20	25	mA
Operating temperature	T _{opr}	-25	_	85	°C
Gate to cathode resistance	R _{GK}		27	33	kΩ
Gate to cathode capacity	C _{GK}	_	0.01	0.1	μF

Recommended Operating Conditions

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

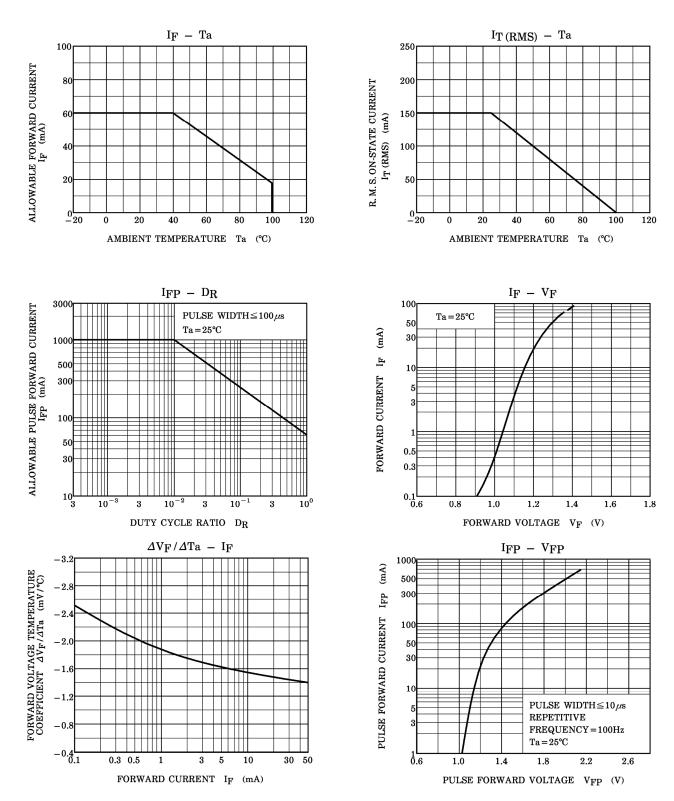
Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition		Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10mA		1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5V		-		10	μA
	Capacitance	CT	V = 0, f = 1MHz			30	_	pF
	Off-state current	IDRM	V _{AK} = 400V R _{GK} = 27kΩ	Ta = 25°C		10	5000	nA
				Ta = 100°C		1	100	μA
	Reverse current	IRRM	V _{KA} = 400V R _{GK} = 27kΩ	Ta = 25°C		10	5000	nA
ы				Ta = 100°C		1	100	μA
Detector	On-state voltage	V _{TM}	I _{TM} = 100mA			0.9	1.3	V
ă	Holding current	Iн	R _{GK} = 27kΩ			0.2	_	mA
	Off-state dv / dt	dv/dt	V_D = 280V, R_{GK} = 27k Ω		5	10	_	V/µs
	Capacitance Cj	C.	V = 0, f = 1MHz	Anode to gate	_	20	_	pF
		Cj		Gate to cathode	_	350	_	μr

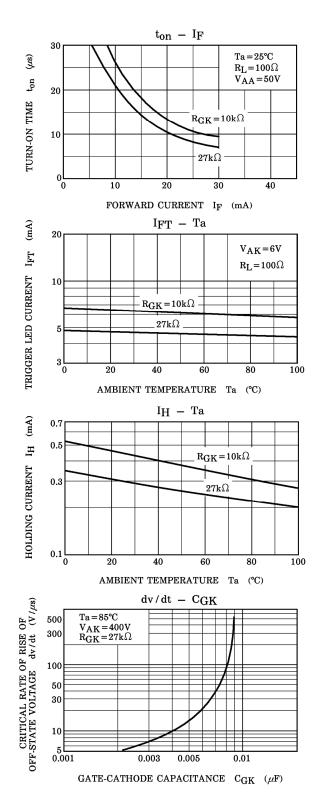
Coupled Characteristics (Ta = 25°C)

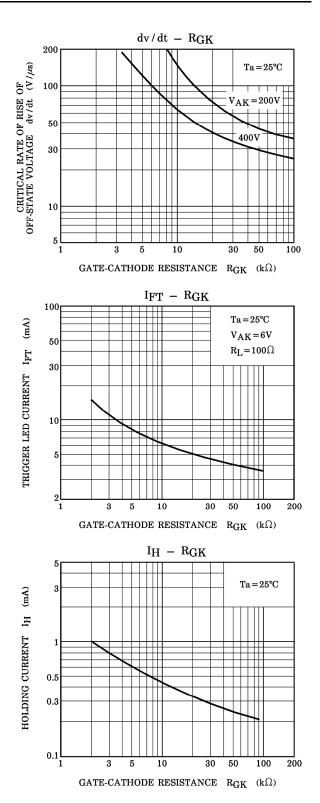
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Trigger LED current	I _{FT}	V_{AK} = 6V, R_{GK} = 27k Ω	—	4	10	mA	
Turn–on time	-on time t_{ON} $I_F = 30 \text{mA}, V_{AA}$ $R_{GK} = 27 \text{k}\Omega$		_	10	_	μs	
Coupled dv/dt	dv/dt	V _S = 500V, R _{GK} = 27kΩ	500	_	_	V/µs	
Capacitance C _S		V _S = 0, f = 1MHz	_	0.8	_	pF	
solation resistance R_S V_S = 500		V _S = 500V	1×10 ¹²	10 ¹⁴	_	Ω	
	BVS	AC, 1 minute	4000	_		V	
Isolation voltage		AC, 1 second, in oil	_	10000	_	V _{rms}	
		DC, 1 minute, in oil	_	10000	_	V _{dc}	

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